

## **KSC2310**

## **High Voltage Power Amplifier**

- Collector-Base Voltage: V<sub>CBO</sub>=200V
  Current Gain Bandwidth Product: f<sub>T</sub>=100MHz



1. Emitter 2. Collector 3. Base

## **NPN Epitaxial Silicon Transistor**

## **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

| Symbol           | Parameter                   | Ratings   | Units |
|------------------|-----------------------------|-----------|-------|
| $V_{CBO}$        | Collector-Base Voltage      | 200       | V     |
| V <sub>CEO</sub> | Collector-Emitter Voltage   | 150       | V     |
| V <sub>EBO</sub> | Emitter-Base Voltage        | 5         | V     |
| I <sub>C</sub>   | Collector Current           | 50        | mA    |
| P <sub>C</sub>   | Collector Power Dissipation | 800       | mW    |
| T <sub>J</sub>   | Junction Temperature        | 150       | °C    |
| T <sub>STG</sub> | Storage Temperature         | -55 ~ 150 | °C    |

## **Electrical Characteristics** $T_a$ =25°C unless otherwise noted

| Symbol                | Parameter                            | Test Condition                                  | Min. | Тур. | Max. | Units |
|-----------------------|--------------------------------------|---|------|------|------|-------|
| BV <sub>CBO</sub>     | Collector-Base Breakdown Voltage     | $I_C=100\mu A, I_E=0$                           | 200  |      |      | V     |
| BV <sub>CEO</sub>     | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> =5mA, I <sub>B</sub> =0          | 150  |      |      | V     |
| BV <sub>EBO</sub>     | Emitter-Base Breakdown Voltage       | $I_E=100\mu A, I_C=0$                           | 5    |      |      | V     |
| I <sub>CBO</sub>      | Collector Cut-off Current            | V <sub>CB</sub> =200V, I <sub>E</sub> =0        |      |      | 0.1  | μΑ    |
| h <sub>FE</sub>       | DC Current Gain                      | V <sub>CE</sub> =5V, I <sub>C</sub> =10mA       | 40   |      | 240  |       |
| V <sub>CE</sub> (sat) | Collector-Emitter Saturation Voltage | I <sub>C</sub> =10mA, I <sub>B</sub> =1mA       |      |      | 0.5  | V     |
| f <sub>T</sub>        | Current Gain Bandwidth Product       | V <sub>CE</sub> =30V, I <sub>C</sub> =10mA      |      | 100  |      | MHz   |
| C <sub>ob</sub>       | Output Capacitance                   | V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz |      | 3.5  | 5    | pF    |

## **h**<sub>FE</sub> Classification

| Classification  | R       | 0        | Y         |
|-----------------|---------|----------|-----------|
| h <sub>FE</sub> | 40 ~ 80 | 70 ~ 140 | 120 ~ 240 |

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# **Typical Characteristics**

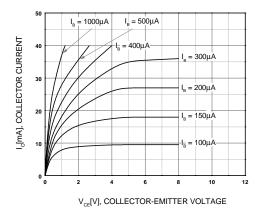


Figure 1. Static Characteristic

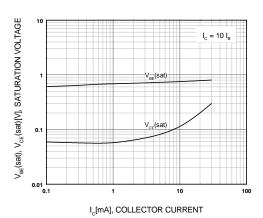


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

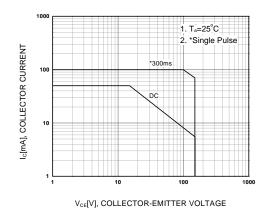
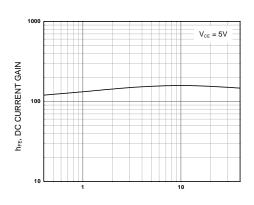


Figure 5. Safe Operating Area



 $I_{\text{c}}[\text{mA}]$ , COLLECTOR CURRENT

Figure 2. DC current Gain

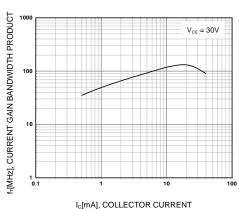


Figure 4. Current Gain Bandwidth Product

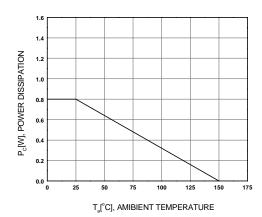


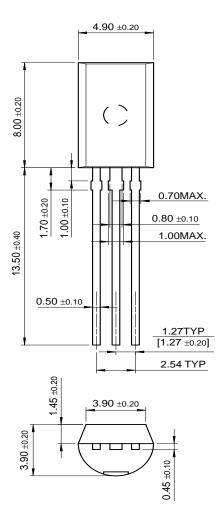
Figure 6. Power Derating

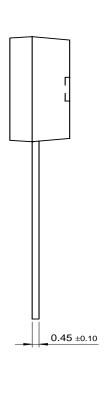
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# **Package Dimensions**

# TO-92L





Dimensions in Millimeters

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| CoolFET™             | FASTr™               | MicroFET™              | PowerTrench <sup>®</sup> | SuperSOT™-6           |
| CROSSVOLT™           | FRFET™               | MicroPak™              | QFET™                    | SuperSOT™-8           |
| DOME™                | GlobalOptoisolator™  | MICROWIRE™             | QS™                      | SyncFET™              |
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